



Diode Module

Features

- A package of series of two diodes
- Heat transfer through alumina ceramic and al9.68 .5 (r)-313.5 (c)bs (and) t 14.96 0 Tw 9-t 14.96 e

Product Summary

Parameter	Value	Unit
V_{RRM}	2000	V
$I_{F(AV)}$ (@ $T_C = 100^\circ\text{C}$)	160	A
I_{FSM} (@ $t_P = 10\text{ms}$)	4480	A
$V_F(\text{Max})$	1.60	V

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	2000	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	2100	V
Average forward current	$T_C = 100^\circ\text{C}$	$I_{F(AV)}$	160	A
Forward surge current	1/2 cycle, Sine wave, 50Hz	I_{FSM}	4480	A
I^2t value for fusing	$T_{vj} = 25^\circ\text{C}$	I^2t	100300	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	



Package Outlines (mm)



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